## SPICE Device Model Si3483CDV



Vishay Siliconix

## P-Channel 20 V (D-S) MOSFET

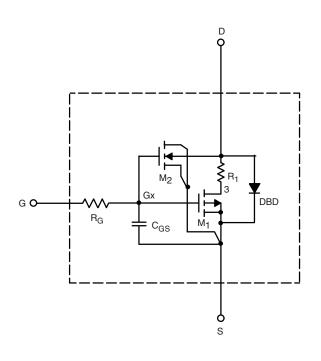
### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C<sub>gd</sub> model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### SUBCIRCUIT MODEL SCHEMATIC

### **CHARACTERISTICS**

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



#### Note

 This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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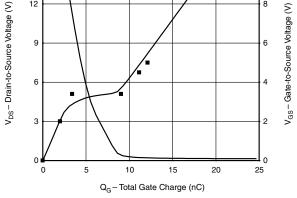
<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$	2.1	-	V
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -6.1 \text{ A}$	0.026	0.027	Ω
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -2 \text{ A}$	0.043	0.044	
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 6.1 A	13	13	S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 4.9 A	- 0.80	- 0.80	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	1030	1000	pF
Output Capacitance	C <sub>oss</sub>		175	170	
Reverse Transfer Capacitance	C <sub>rss</sub>		134	140	
Total Gate Charge	0	$V_{DS}$ = - 15 V, $V_{GS}$ = - 10 V, $I_D$ = - 6.1 A	20	22	nC
	Qg		10.70	11.5	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -15 V$ , $V_{GS} = -4.5 V$ , $I_D = -6.1 A$	3.4	3.4	
Gate-Drain Charge	Q <sub>gd</sub>	] [	5.7	5.7	

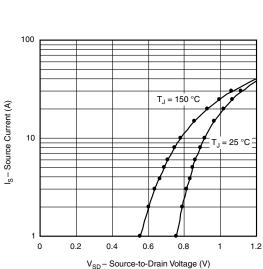
Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

SHAY www.vishay.com Vishay Siliconix COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted) 5 25 V<sub>GS</sub> : 10, 7, 6, 5 V 20 4 T<sub>C</sub> = 125 °C I<sub>D</sub>- Drain Current (A) I<sub>D</sub> – Drain Current (A) 15 3  $V_{GS} = 4 V$ - 55 °C 10 2 5 1  $V_{GS} = 3 V$ 25 °C 0 C 2.5 3.0 0.0 0.5 1.0 1.5 2.0 0 1 2 3 4 V<sub>DS</sub> - Drain-to-Source Voltage (V) V<sub>GS</sub> - Gate-to-Source Voltage (V) 0.10 1800 ļ 1500 0.08  $R_{DS(on)}$  – On-Resistance ( $\Omega$ ) C<sub>iss</sub> C – Capacitance (pF) 1200 0.06 V<sub>GS</sub> = 4.5 V 900 0.04 600  $V_{GS} = 10 V$ Coss 0.02 300 C<sub>rss</sub> 0.00 0 0 5 15 20 25 0 5 25 10 10 20 30 15 I<sub>D</sub> - Drain Current (A) V<sub>DS</sub> - Drain-to-Source Voltage (V) 100 15 10 V<sub>DS</sub> V<sub>GS</sub> 12 8 T<sub>J</sub> = 150 °C





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#### Note

• Dots and squares represent measured data.

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